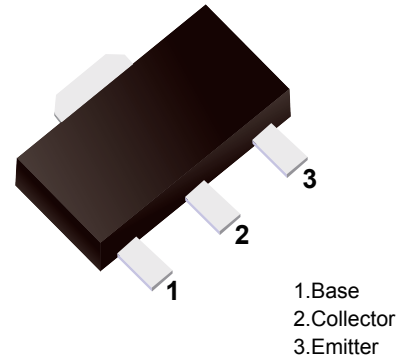


PNP Transistors

■ Features

- NPN Complements to BCX54,BCX55,BCX56
- Low Voltage
- High Current



■ Simplified outline(SOT-89)

■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	BCX51	-45	V
	BCX52	-60	V
	BCX53	-100	V
Collector-emitter voltage	BCX51	-45	V
	BCX52	-60	V
	BCX53	-80	V
Emitter-base voltage	VEBO	-5	V
Collector current	IC	-1	A
Peak collector current	ICM	-1.5	A
Peak base current	IBM	-200	mA
Total power dissipation	P _{tot}	1.3	W
Storage temperature	T _{stg}	-65 to +150	°C
Junction temperature	T _j	150	°C
Operating ambient temperature	T _{amb}	-65 to +150	°C
Thermal resistance from junction to ambient	R _{th(j-a)}	94	K/W
Thermal resistance from junction to solder point	R _{th(j-s)}	14	K/W

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	I _{CBO}	V _{CB} = -30 V, I _E = 0			-100	nA
		V _{CB} = -30 V, I _E = 0; T _j = 125°C			-10	uA
Emitter cutoff current	I _{EBO}	V _{EB} = -5 V, I _C = 0			-100	nA
DC current gain	h _{FE}	I _C = -5 mA; V _{CE} = -2 V	63			
		I _C = -150 mA; V _{CE} = -2 V	63		250	
		I _C = -500 mA; V _{CE} = -2 V	40			
DC current gain BCX51-10,BCX52-10,BCX53-10 BCX51-16,BCX52-16,BCX53-16	h _{FE}	I _C = -150 mA; V _{CE} = -2 V	63		160	
		I _C = -150 mA; V _{CE} = -2 V	100		250	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -500 mA; I _B = -50 mA			-500	mV
Base to emitter voltage	V _{BE}	I _C = -500 mA; V _{CE} = -2 V			-1	V
Transition frequency	f _T	I _C = -10 mA; V _{CE} = -5 V; f = 100 MHz		50		MHz

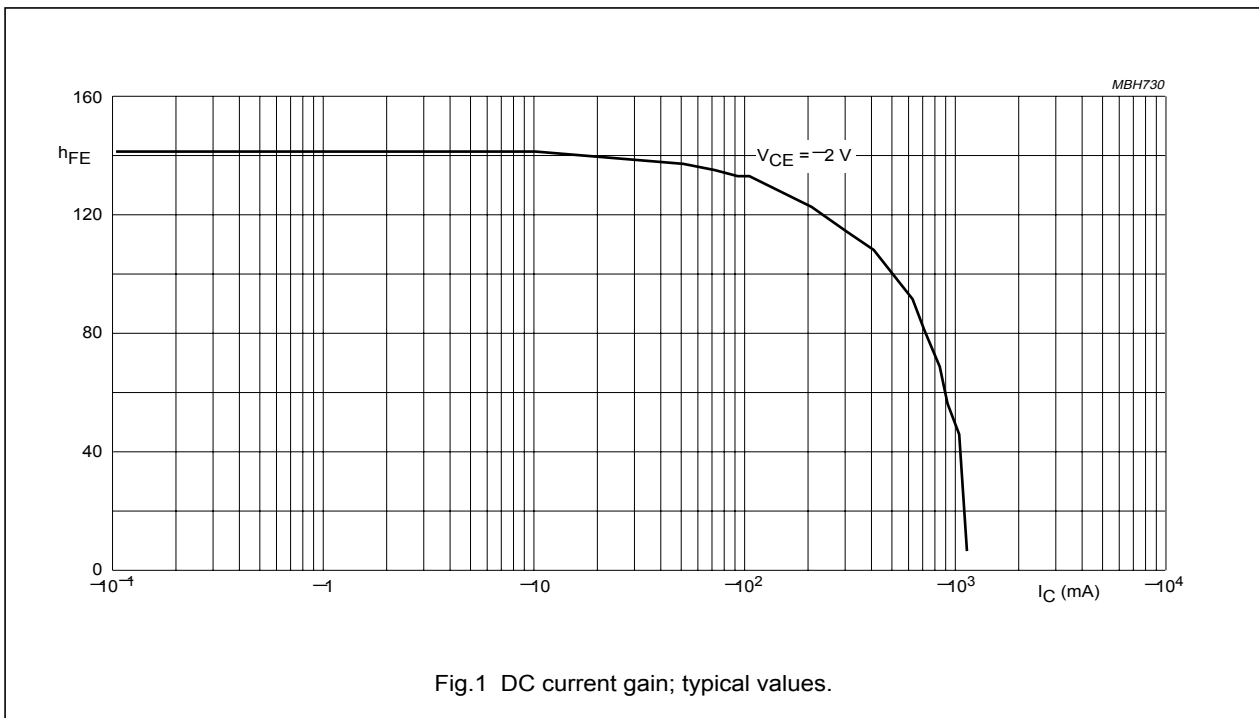
hFE Classification

TYPE	BCX51	BCX51-10	BCX51-16
Marking	AA	AC	AD

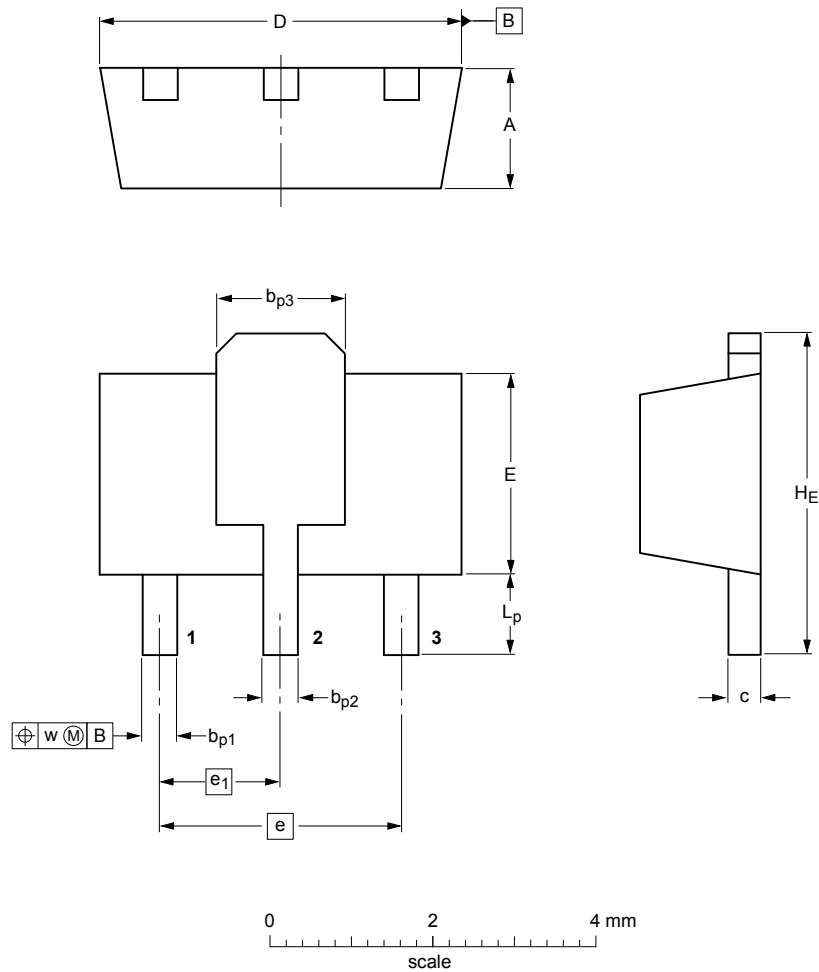
TYPE	BCX52	BCX52-10	BCX52-16
Marking	AE	AG	AM

TYPE	BCX53	BCX53-10	BCX53-16
Marking	AH	AK	AL

Typical Characteristics



■ SOT-89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b_{p1}	b_{p2}	b_{p3}	c	D	E	e	e_1	H_E	L_p	w
mm	1.6	0.48	0.53	1.8	0.44	4.6	2.6	3.0	1.5	4.25	1.2	0.13
	1.4	0.35	0.40	1.4	0.23	4.4	2.4					